

SKM150GAR12T4



SEMITRANS® 2

Fast IGBT4 Modules

SKM150GAR12T4

Features

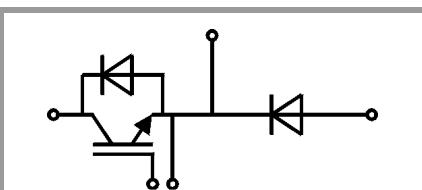
- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, selflimiting to $6 \times I_{Cnom}$
- Soft switching 4. Generation CALdiode (CAL4)
- UL recognized, file no. E63532

Typical Applications*

- Electronic welders
- DC/DC – converter
- Brake chopper
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	232	A
		$T_c = 80^\circ\text{C}$	179	A
I_{Cnom}			150	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		450	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
	$V_{GE} \leq 15\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
T_j			-40 ... 175	$^\circ\text{C}$
Inverse diode				
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	189	A
		$T_c = 80^\circ\text{C}$	141	A
I_{Fnom}			150	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		450	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		900	A
T_j			-40 ... 175	$^\circ\text{C}$
Freewheeling diode				
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	189	A
		$T_c = 80^\circ\text{C}$	141	A
I_{Fnom}			150	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		450	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		900	A
T_j			-40 ... 175	$^\circ\text{C}$
Module				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$		200	A
T_{stg}			-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.80	2.05		V
		$T_j = 150^\circ\text{C}$	2.20	2.40		V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.8	0.9		V
		$T_j = 150^\circ\text{C}$	0.7	0.8		V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	6.67	7.67		m Ω
		$T_j = 150^\circ\text{C}$	10.00	10.67		m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 6\text{ mA}$		5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3		mA
		$T_j = 150^\circ\text{C}$				mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	9.3			nF
C_{oes}		$f = 1\text{ MHz}$	0.58			nF
C_{res}		$f = 1\text{ MHz}$	0.51			nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		850			nC
R_{Gint}	$T_j = 25^\circ\text{C}$		5.00			Ω

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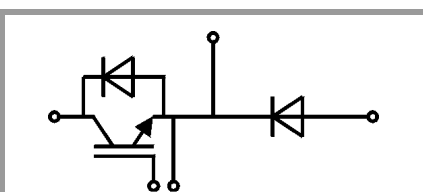
Typical Applications*

- Electronic welders
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- Brake chopper
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		180		ns
t_r	$I_C = 150\text{ A}$	$T_j = 150^\circ\text{C}$		42		ns
E_{on}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		19.2		mJ
$t_{d(off)}$	$R_{G\ on} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		410		ns
t_f	$R_{G\ off} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		72		ns
E_{off}	$di/dt_{on} = 3400\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		15.8		mJ
	$di/dt_{off} = 1750\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per IGBT				0.19	K/W
Inverse diode						
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25^\circ\text{C}$		2.14	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.07	2.38	V
	chiplevel					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
	chiplevel	$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		5.6	6.4	m Ω
	chiplevel	$T_j = 150^\circ\text{C}$		7.8	8.5	m Ω
I_{RRM}	$I_F = 150\text{ A}$	$T_j = 150^\circ\text{C}$		120		A
Q_{rr}	$di/dt_{off} = 3100\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		31.3		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		13		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per diode				0.31	K/W
Freewheeling diode						
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25^\circ\text{C}$		2.14	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.07	2.38	V
	chiplevel					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
	chiplevel	$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		5.6	6.4	m Ω
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Q_{rr}	$di/dt_{off} = 3100\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		31.3		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		13		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per Diode				0.31	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.65		m Ω
		$T_c = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6			3	5	Nm
M_t		to terminals M5		2.5	5	Nm
						Nm
w					160	g



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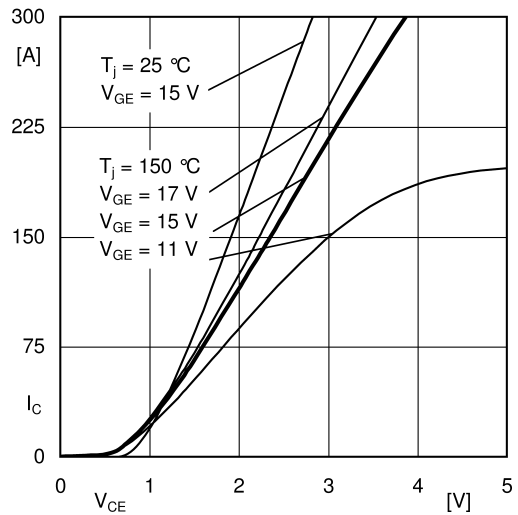


Fig. 1: Typ. output characteristic, inclusive $R_{CC+EE'}$

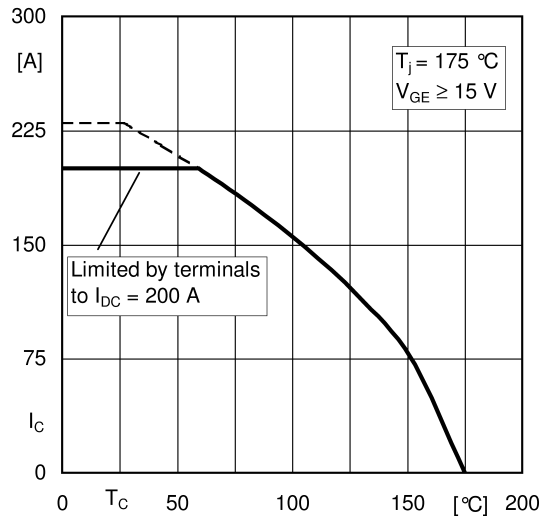


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

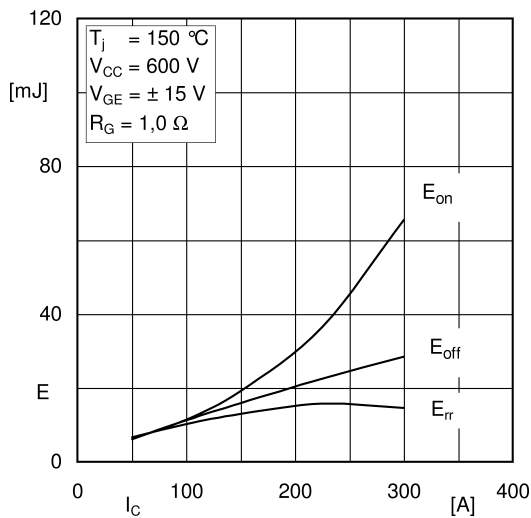


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

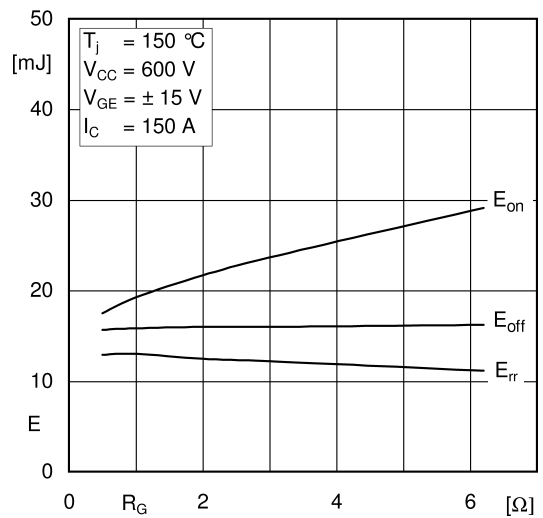


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

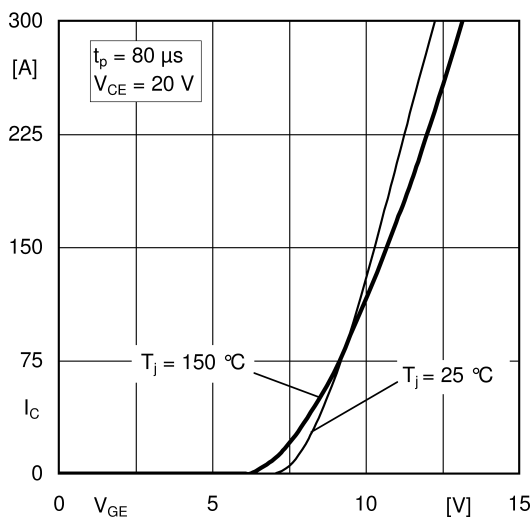


Fig. 5: Typ. transfer characteristic

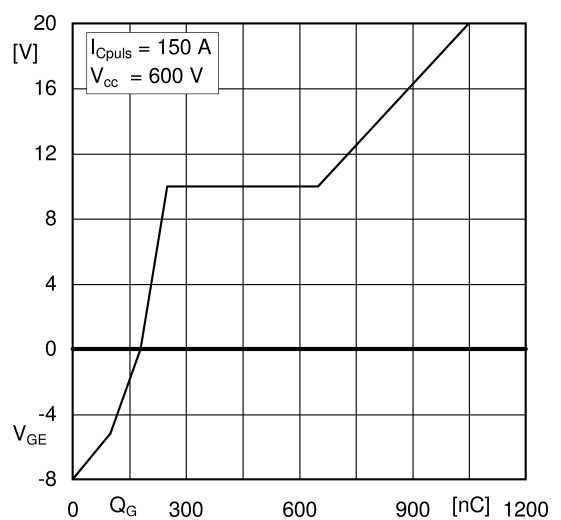


Fig. 6: Typ. gate charge characteristic

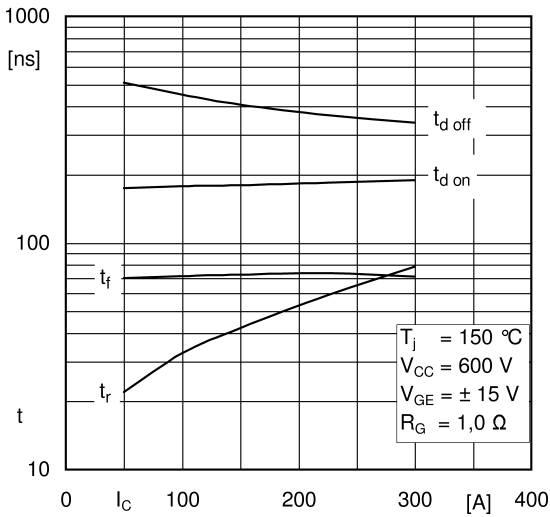


Fig. 7: Typ. switching times vs. I_C

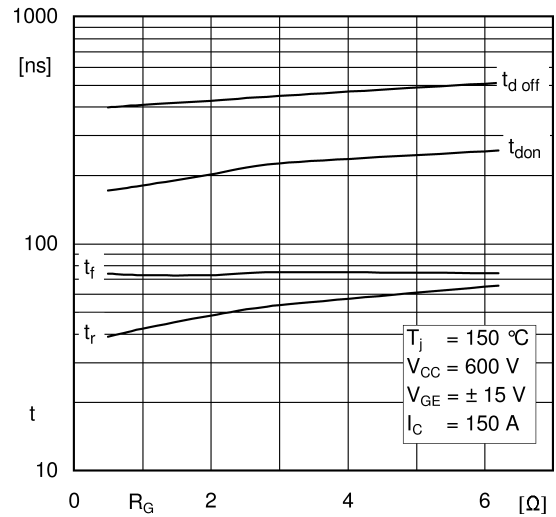


Fig. 8: Typ. switching times vs. gate resistor R_G

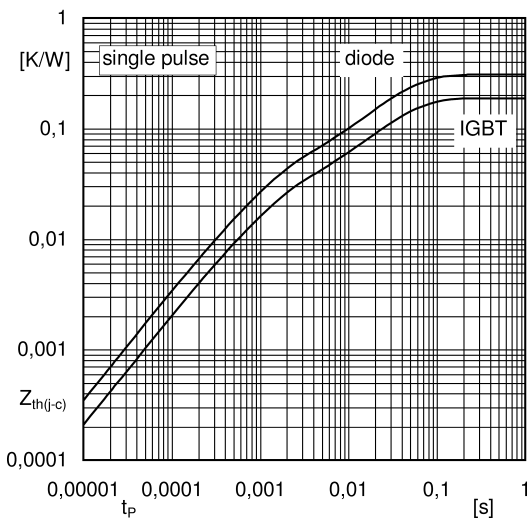


Fig. 9: Transient thermal impedance

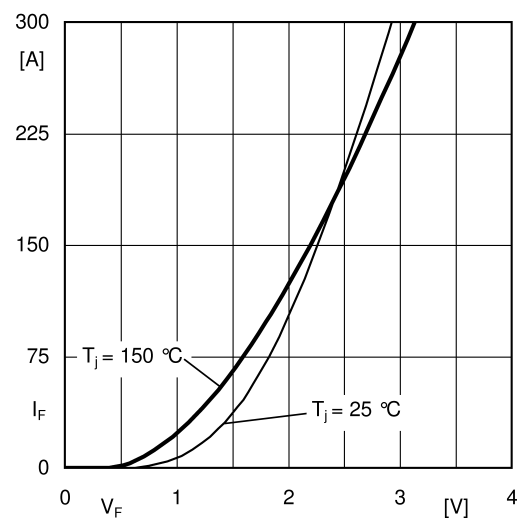


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}

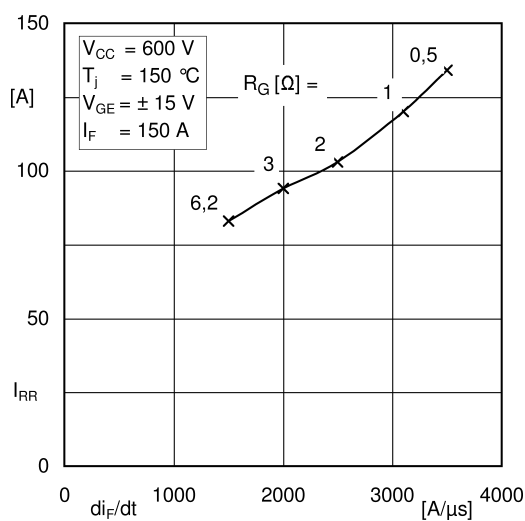


Fig. 11: CAL diode peak reverse recovery current

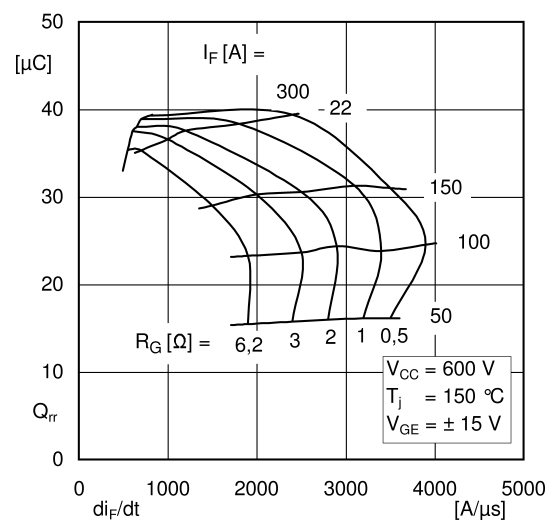
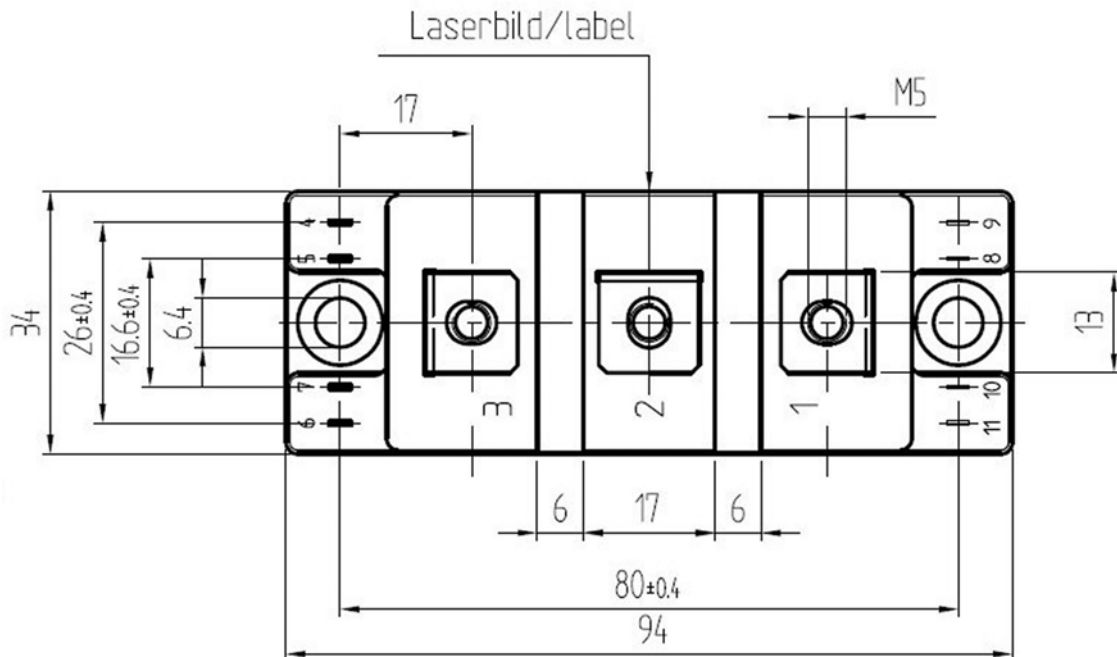
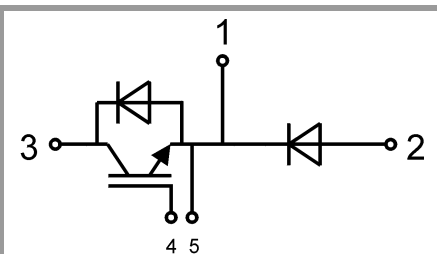


Fig. 12: Typ. CAL diode peak reverse recovery charge

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.